



P-channel Enhancement Mode Mosfet

CX4435

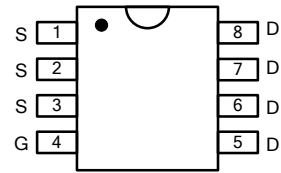
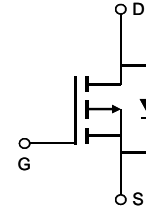
The 4435 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

- $R_{DS(ON)} < 18m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 26m\Omega @ V_{GS} = -4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Marking and pin assignment

ABSOLUTE MAXIMUM RATINGS($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit	
Drain-source Voltage	V_{DS}	-30	V	
Gate-source Voltage	V_{GS}	± 20	V	
Drain Current	I_D	$T_A = 25^\circ C$ @ Steady State	-10	A
		$T_A = 70^\circ C$ @ Steady State	-8	
Pulsed Drain Current ^A	I_{DM}	-50	A	
Total Power Dissipation @ $T_A = 25^\circ C$	P_D	3.0	W	
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	42	$^\circ C / W$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ C$	